

FOUO 11979260

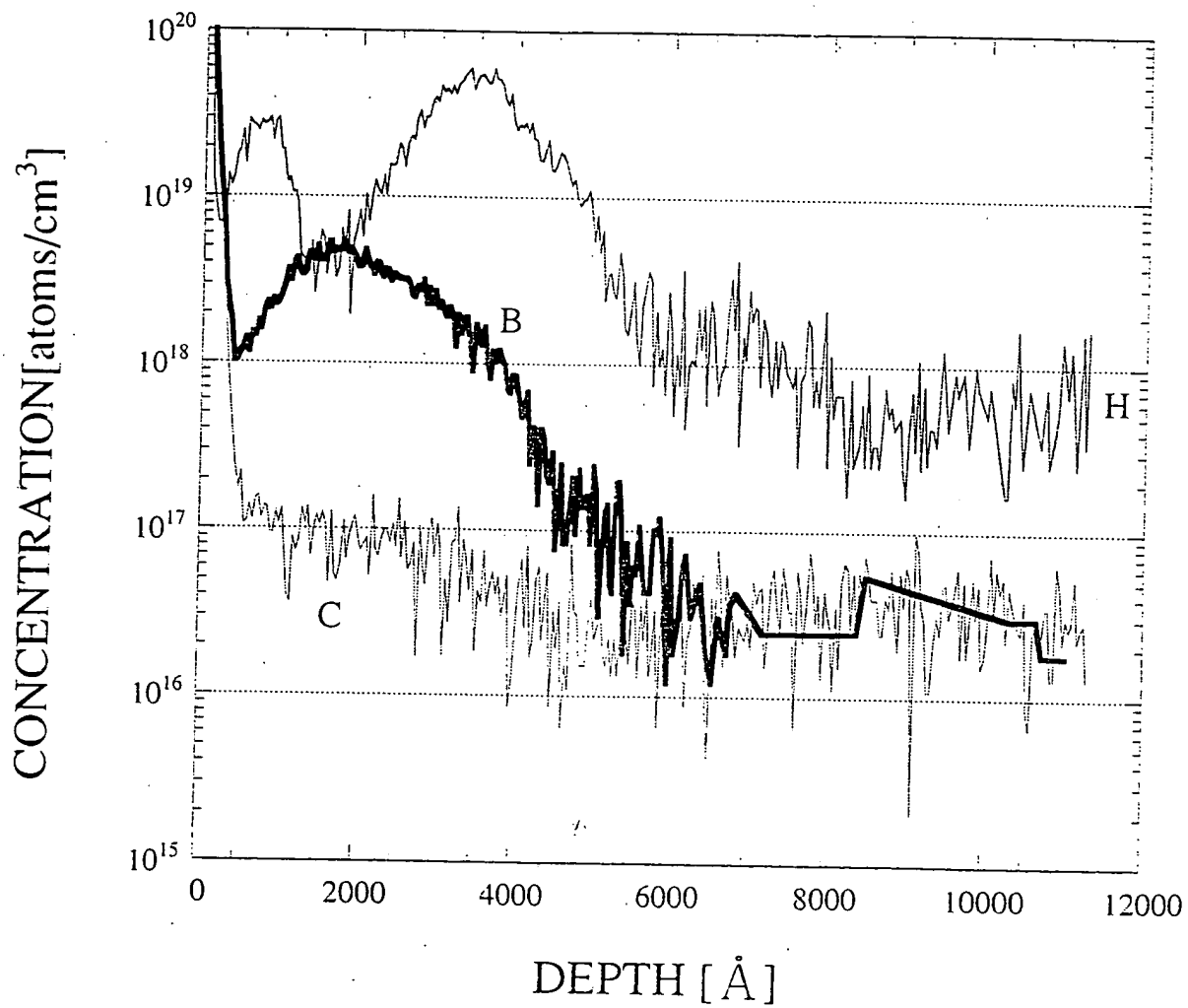


Fig 1

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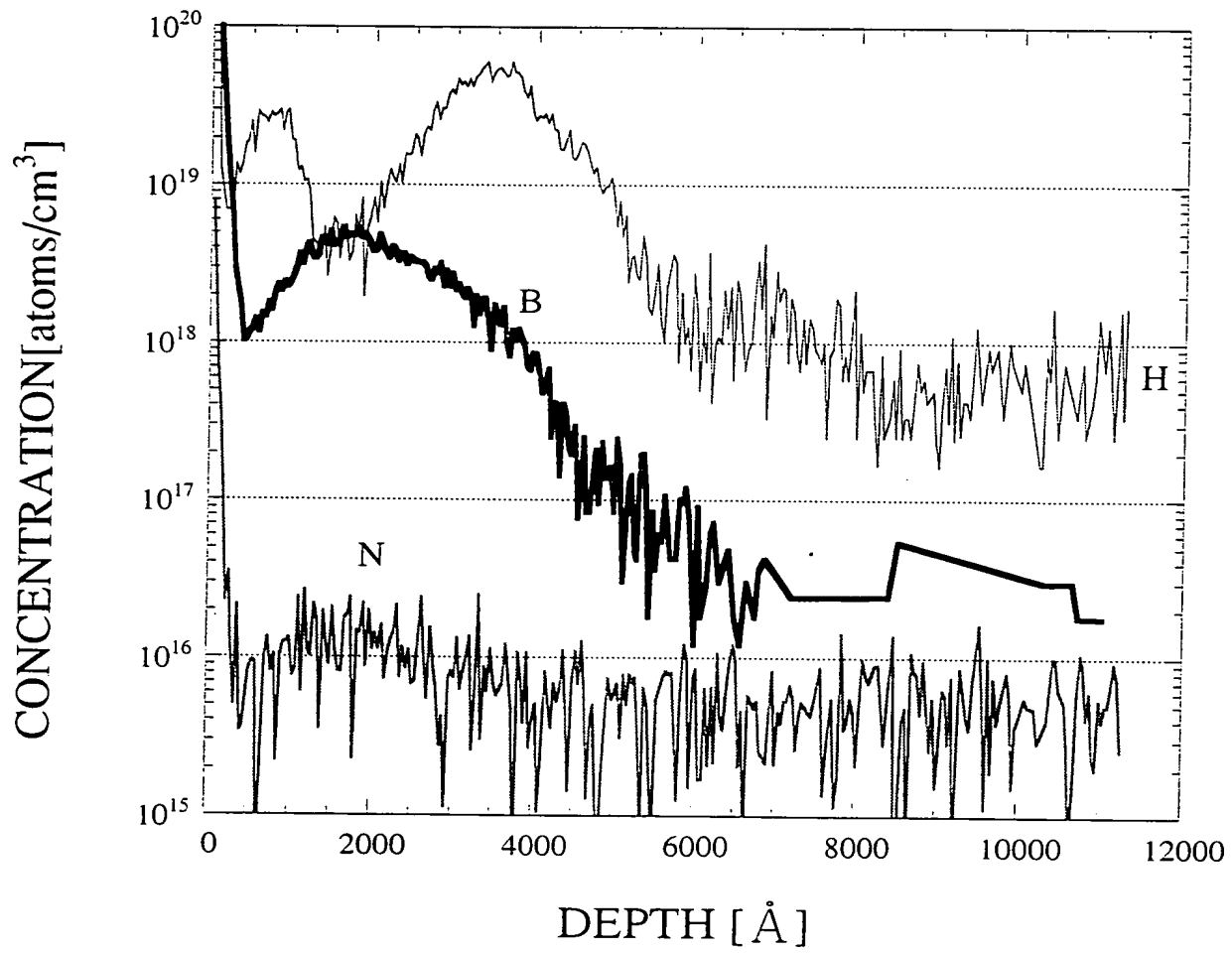


Fig. 2

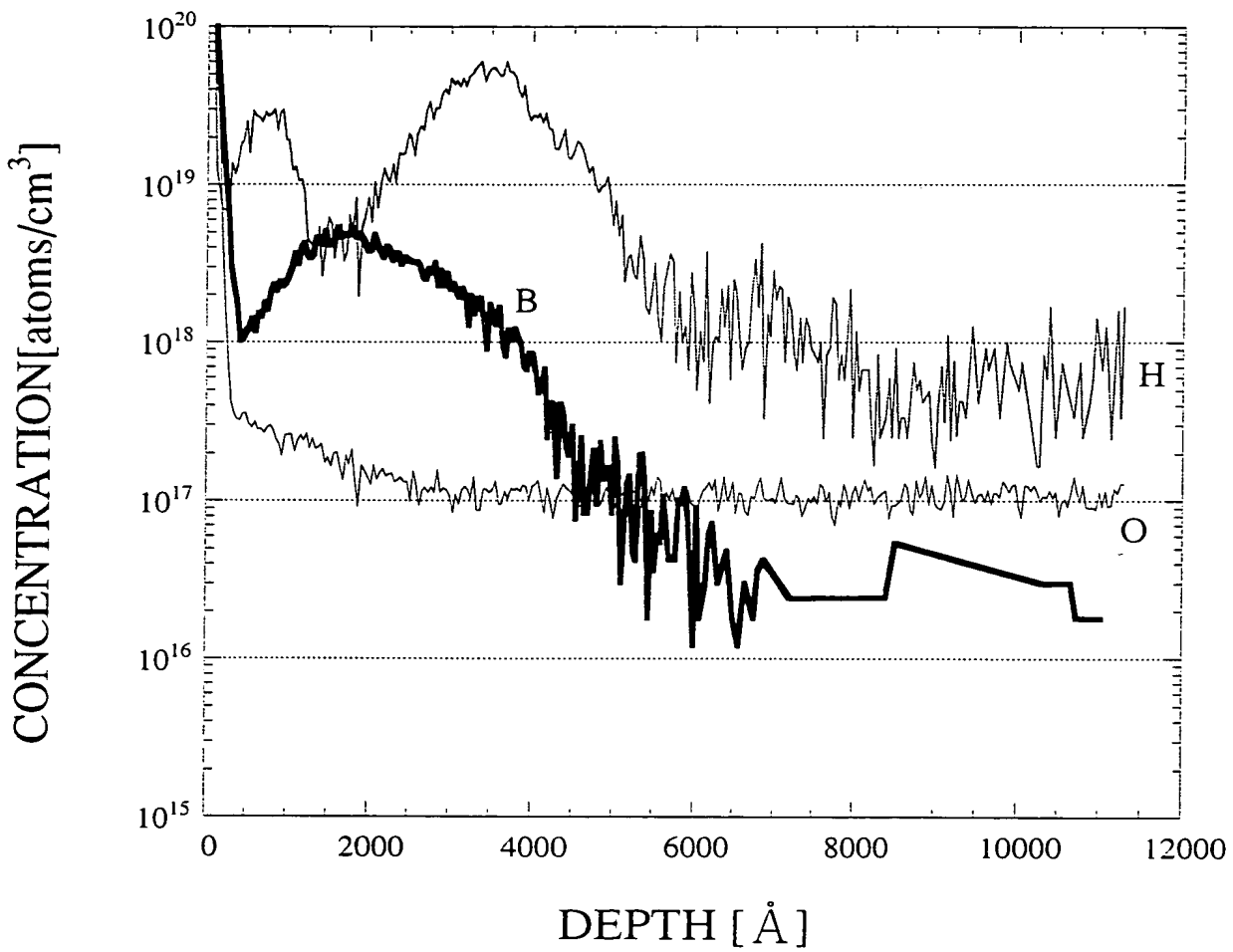


Fig. 3

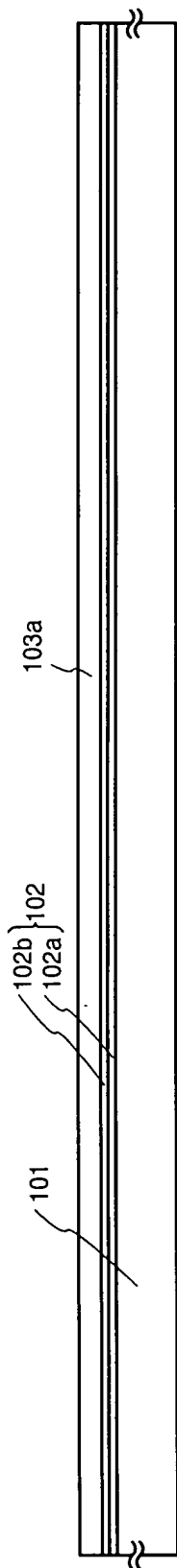


Fig. 4A

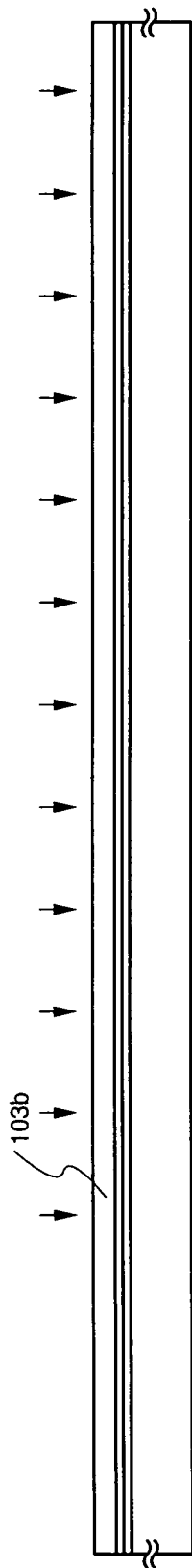


Fig. 4B

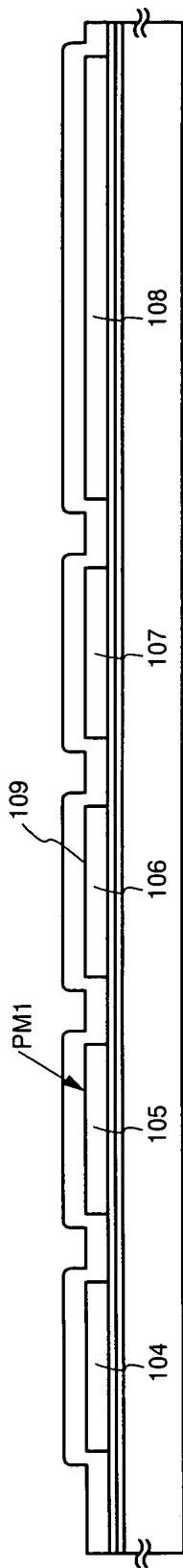


Fig. 4C

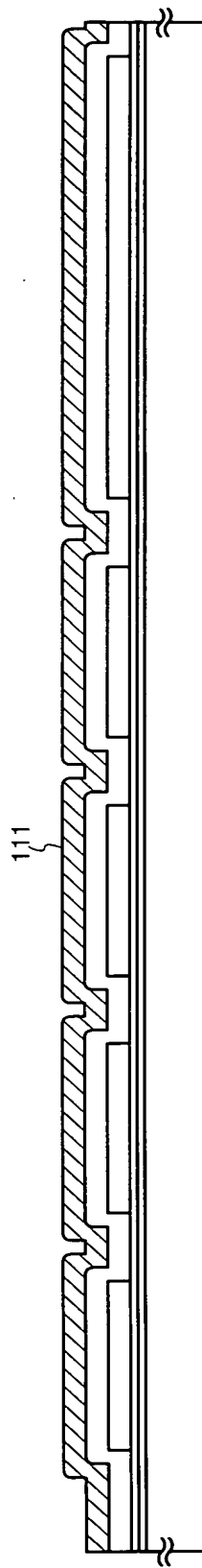


Fig. 4D

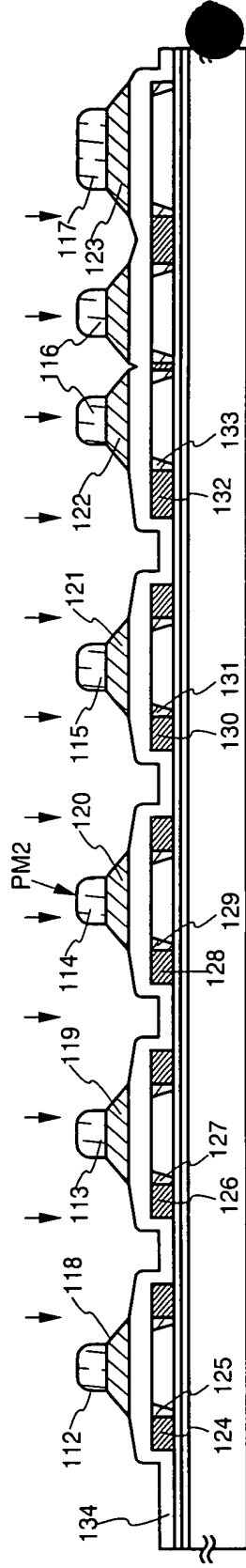


Fig. 5A

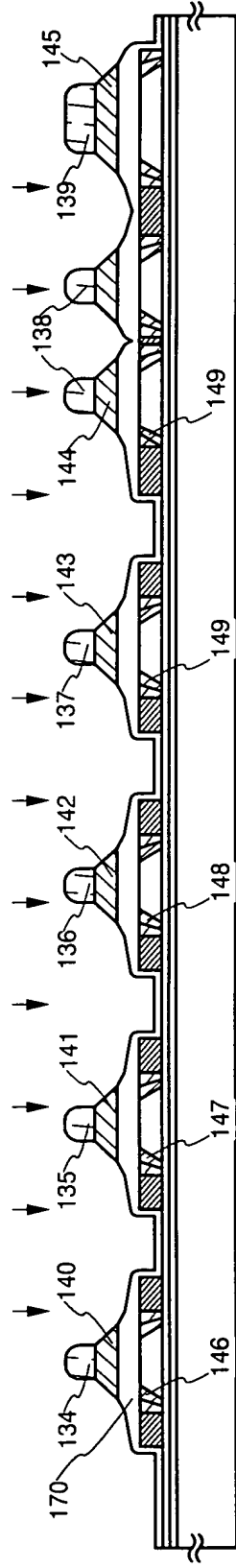


Fig. 5B

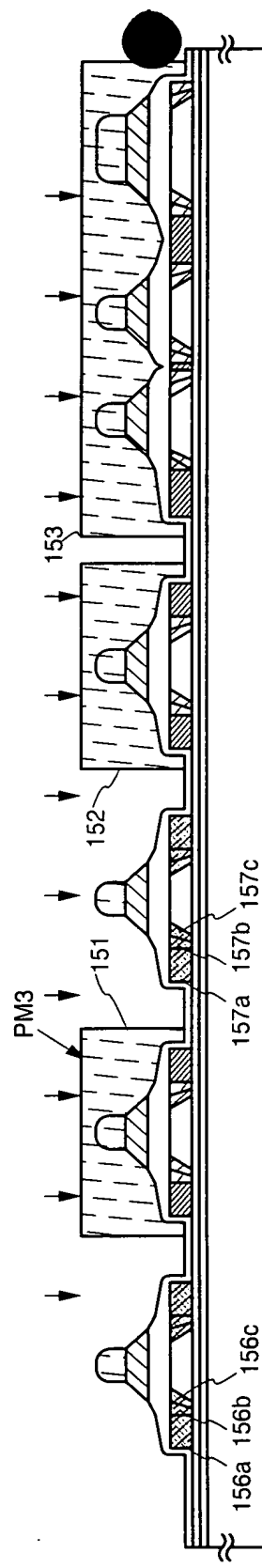


Fig. 5C

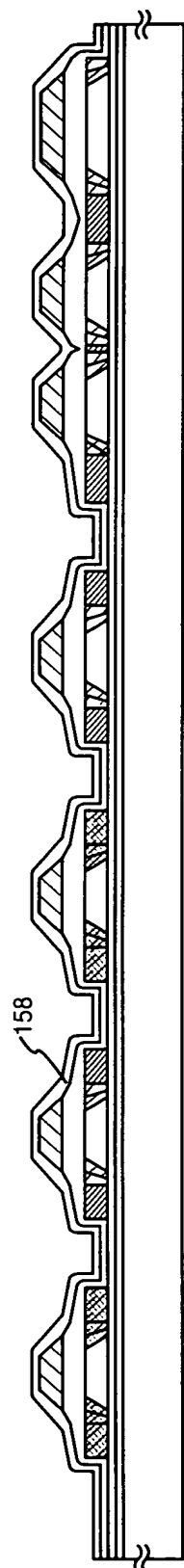


Fig. 6A

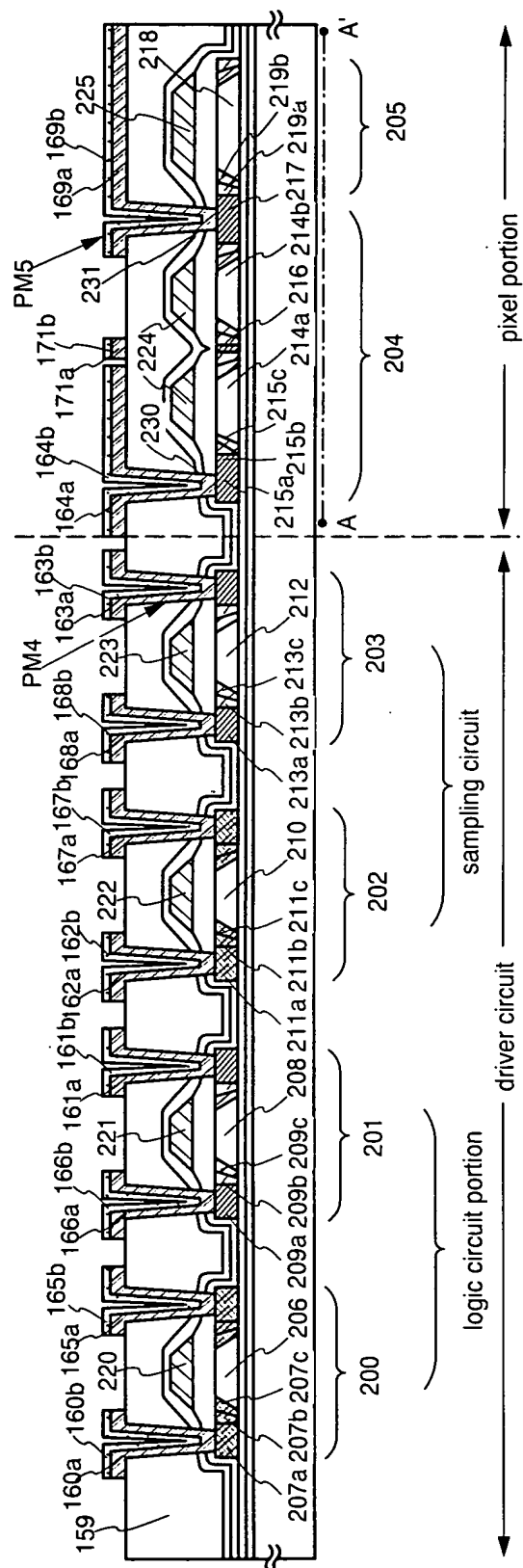


Fig. 6B

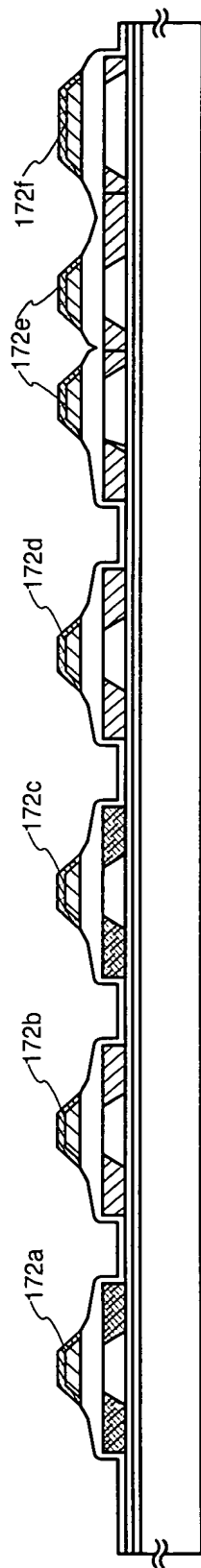


Fig. 7A

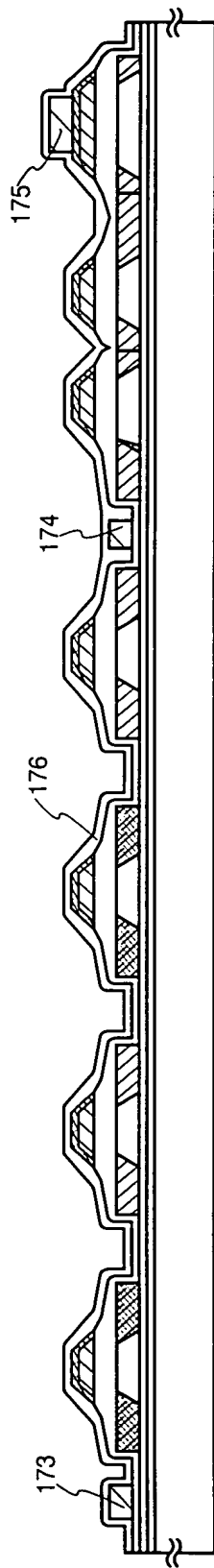


Fig. 7B

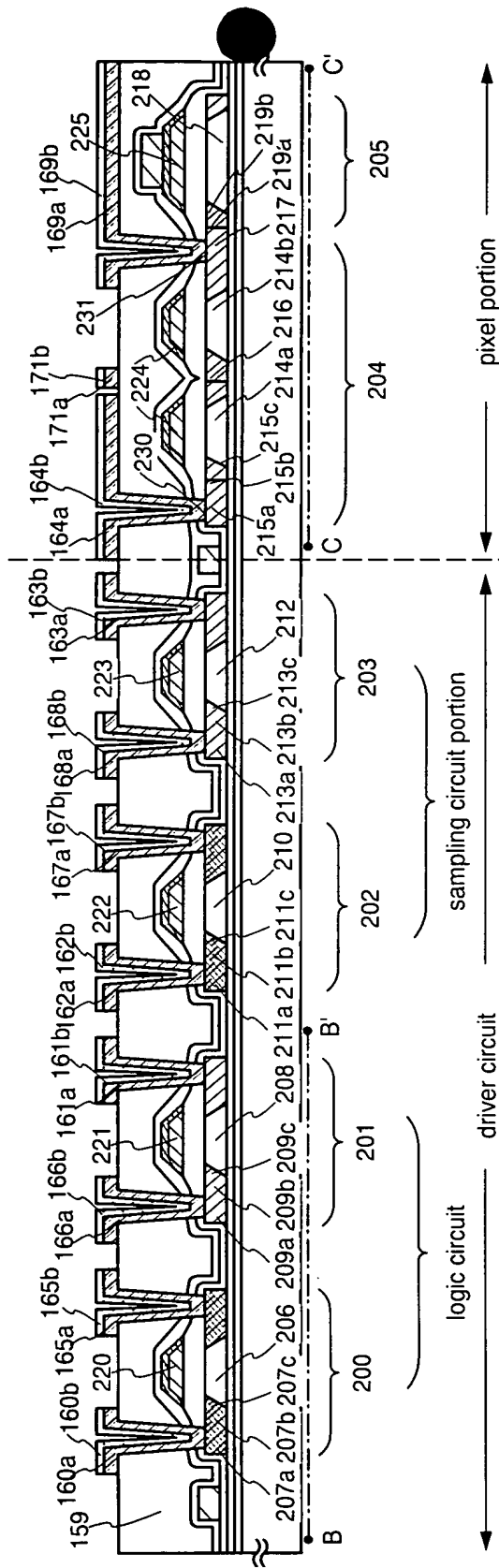


Fig. 7C

Fig. 8A

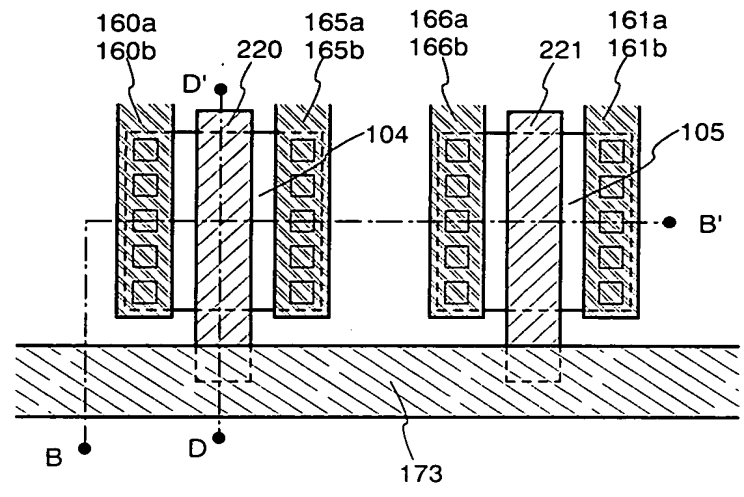
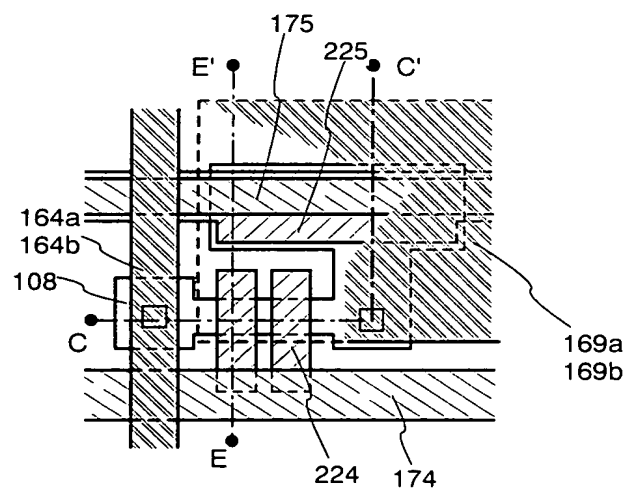


Fig. 8B



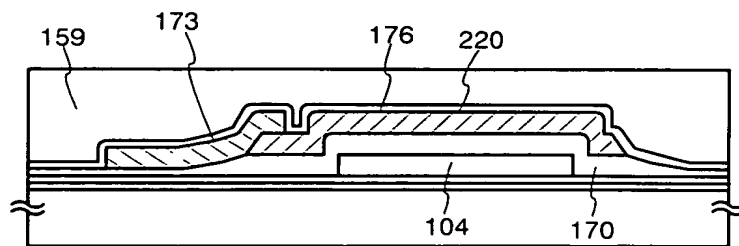


Fig. 9A

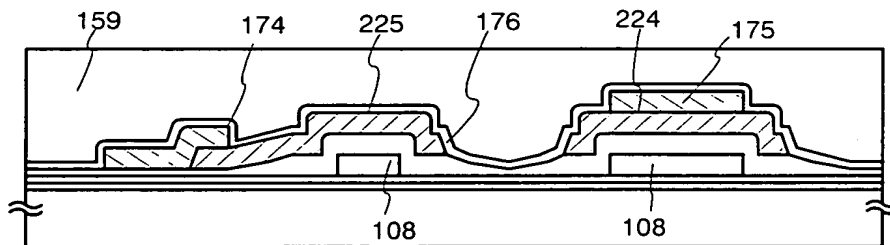


Fig. 9B

Fig. 10A

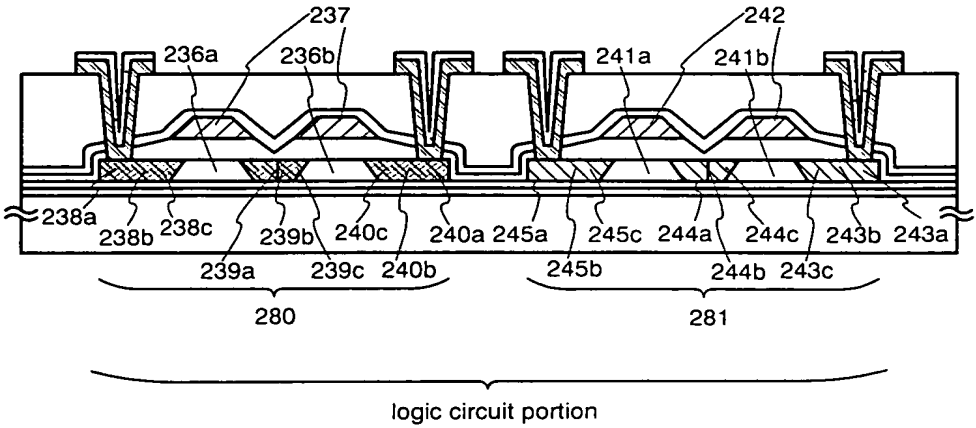


Fig. 10B

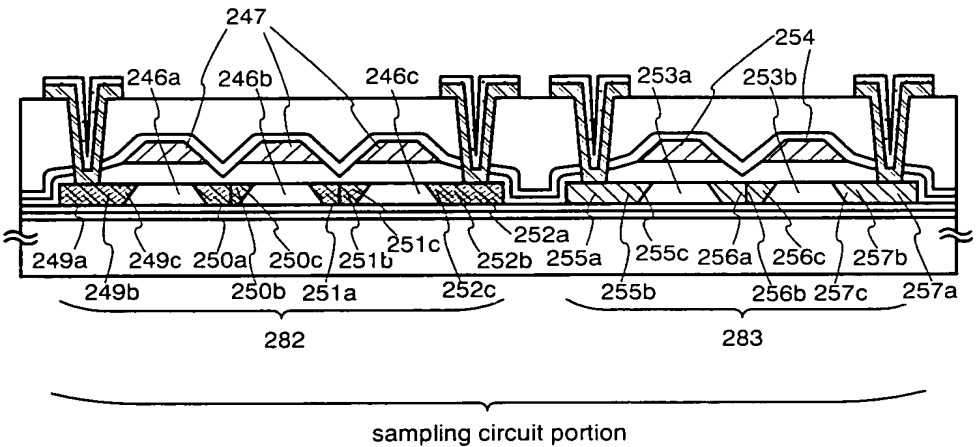


Fig. 11A

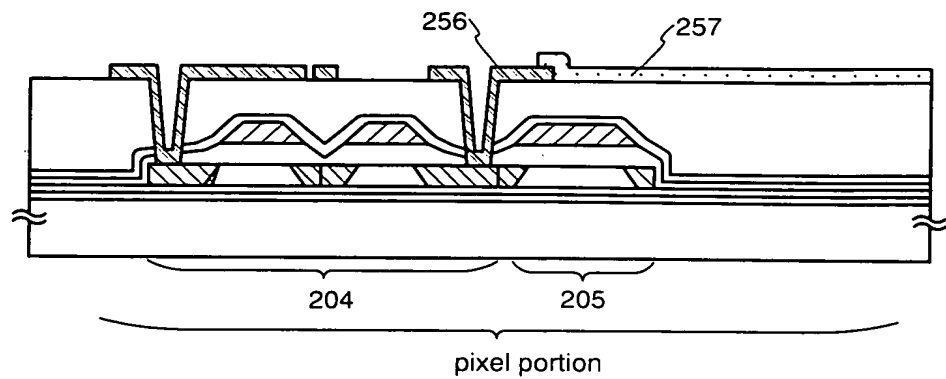


Fig. 11B

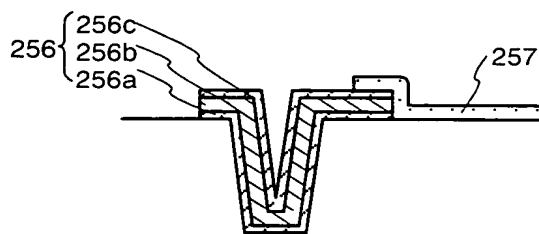


Fig. 11C

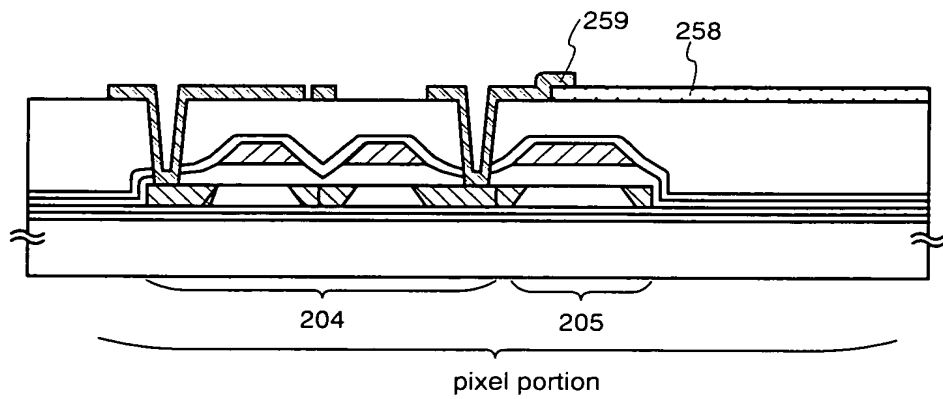
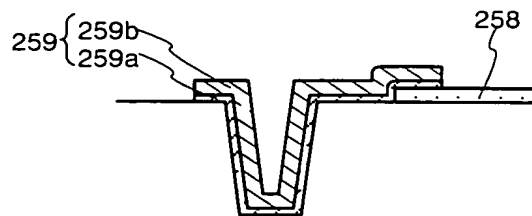


Fig. 11D



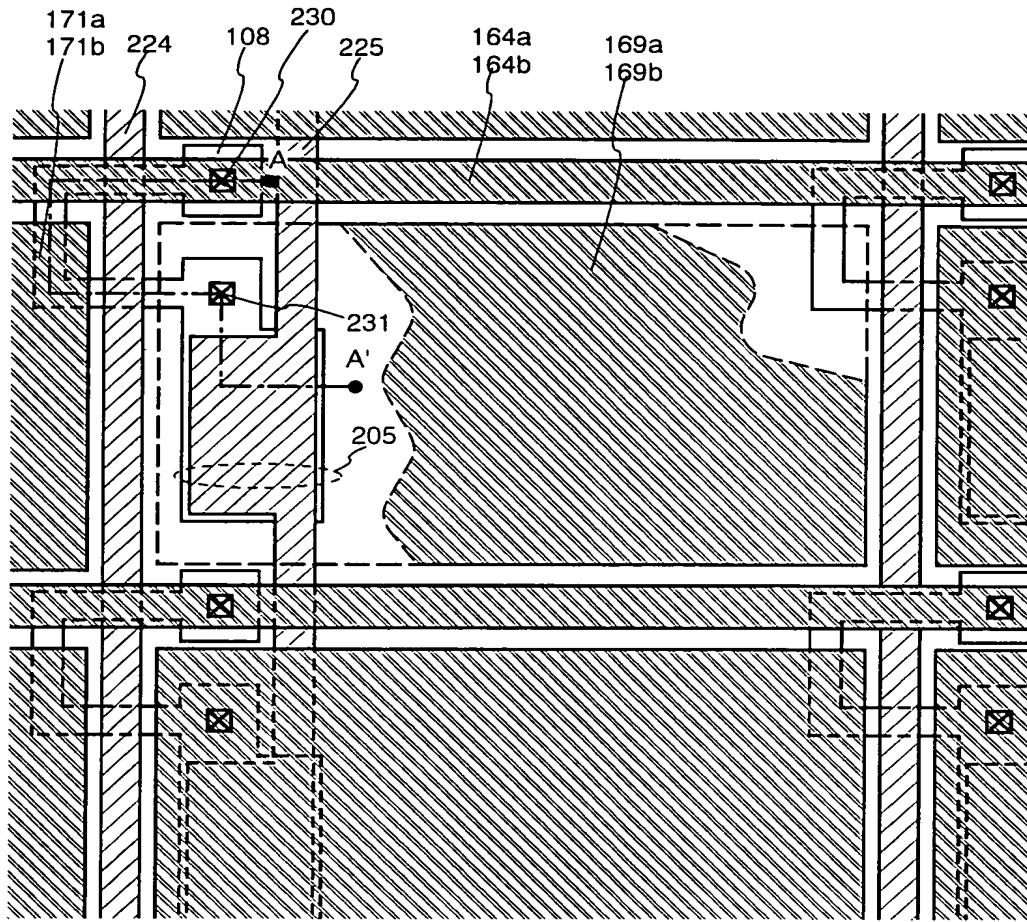
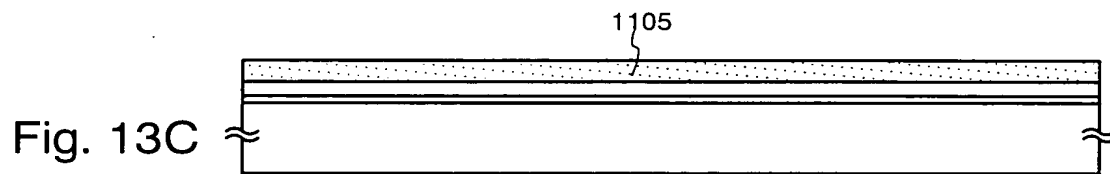
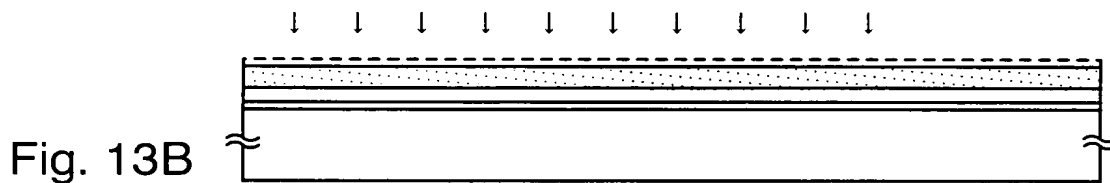
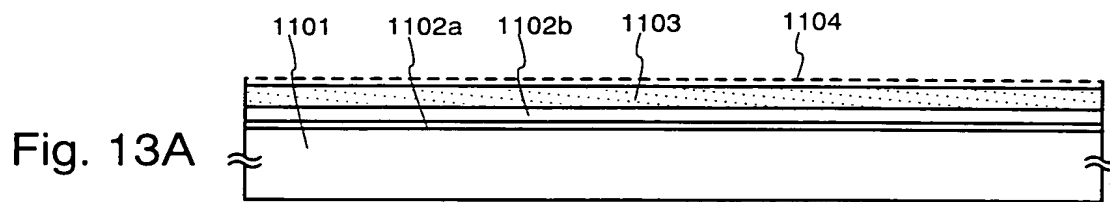


Fig. 12



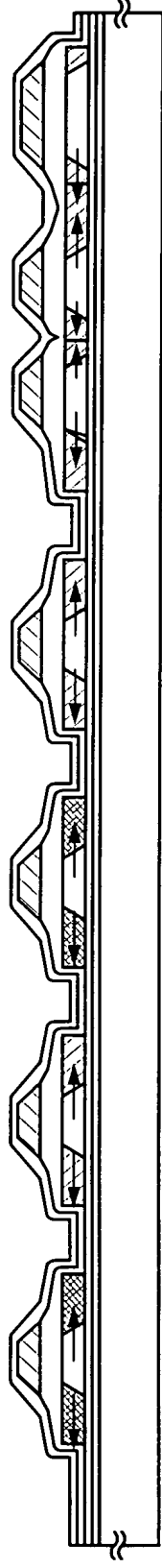


Fig. 14

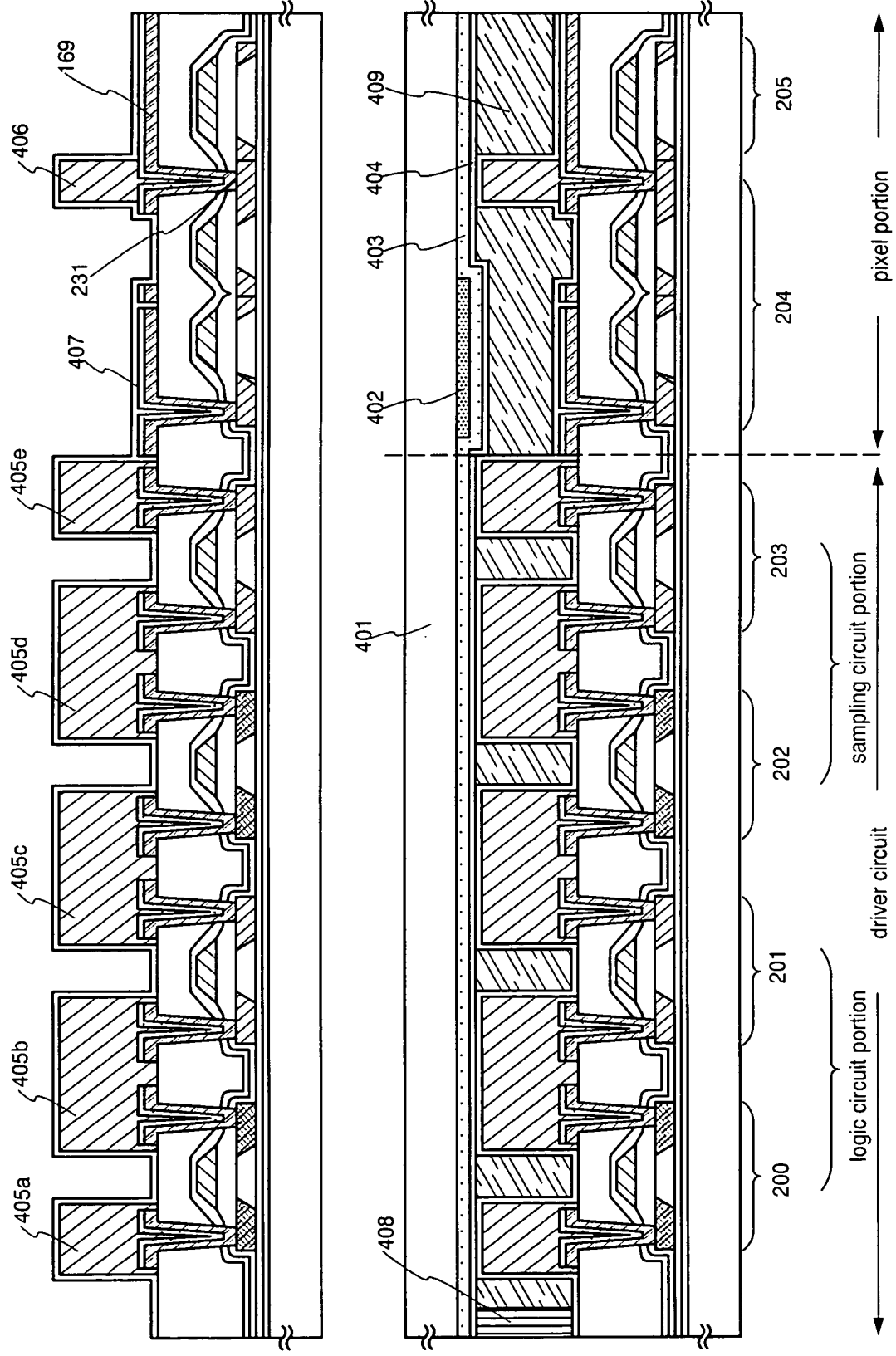


Fig. 15

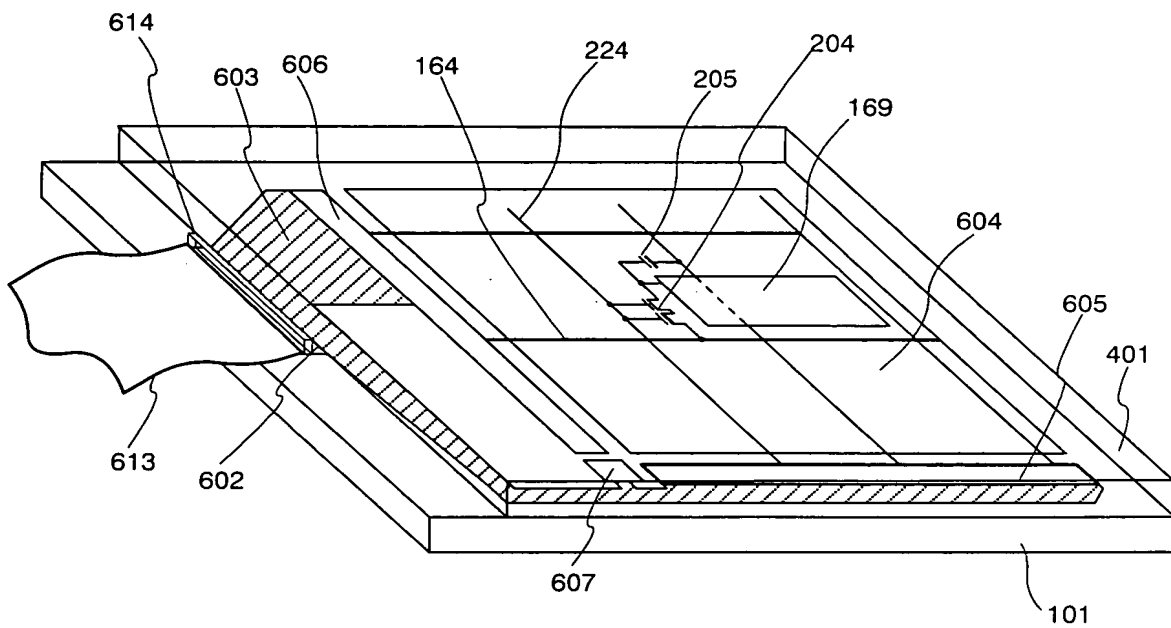


Fig. 16

Fig. 17A

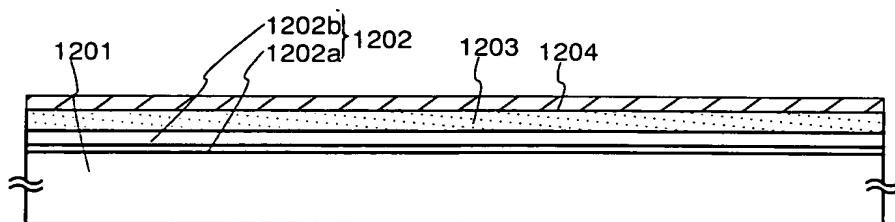


Fig. 17B

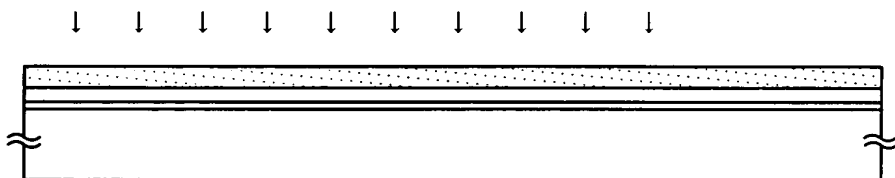
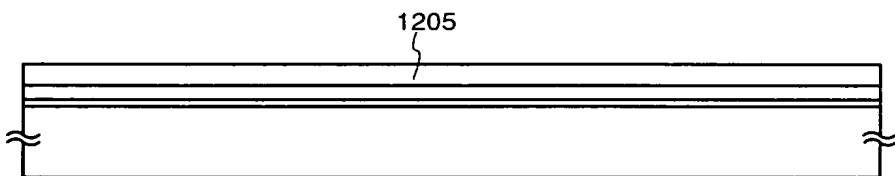


Fig. 17C



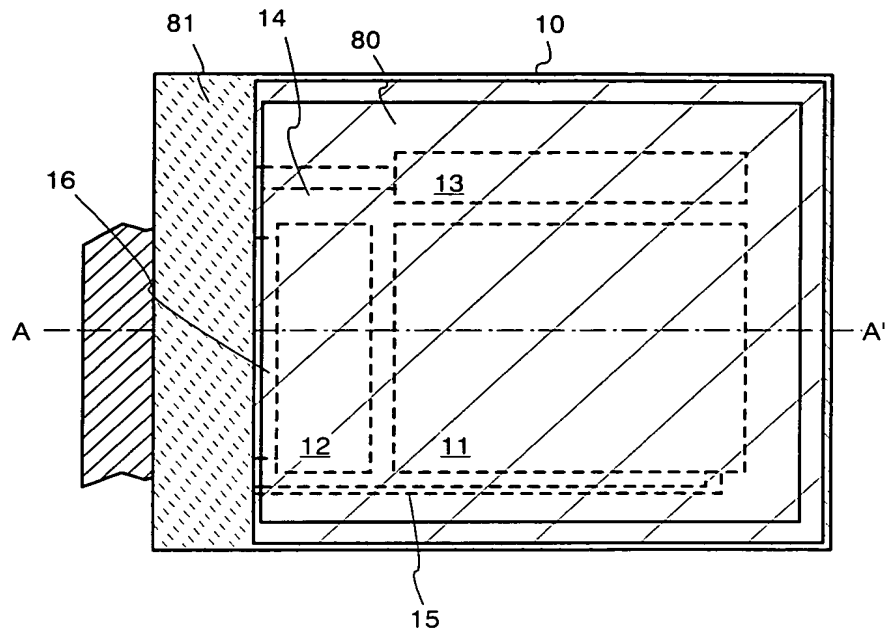


Fig. 18A

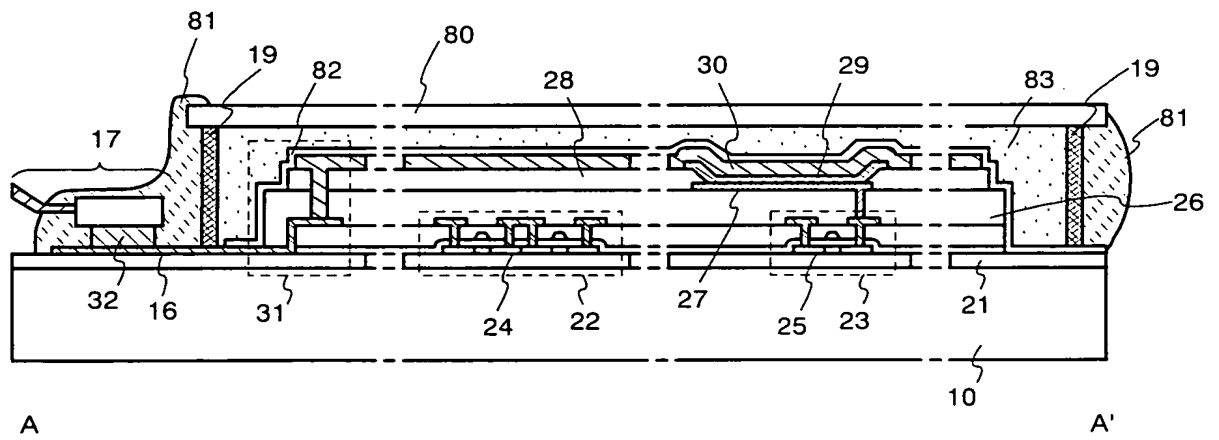


Fig. 18B

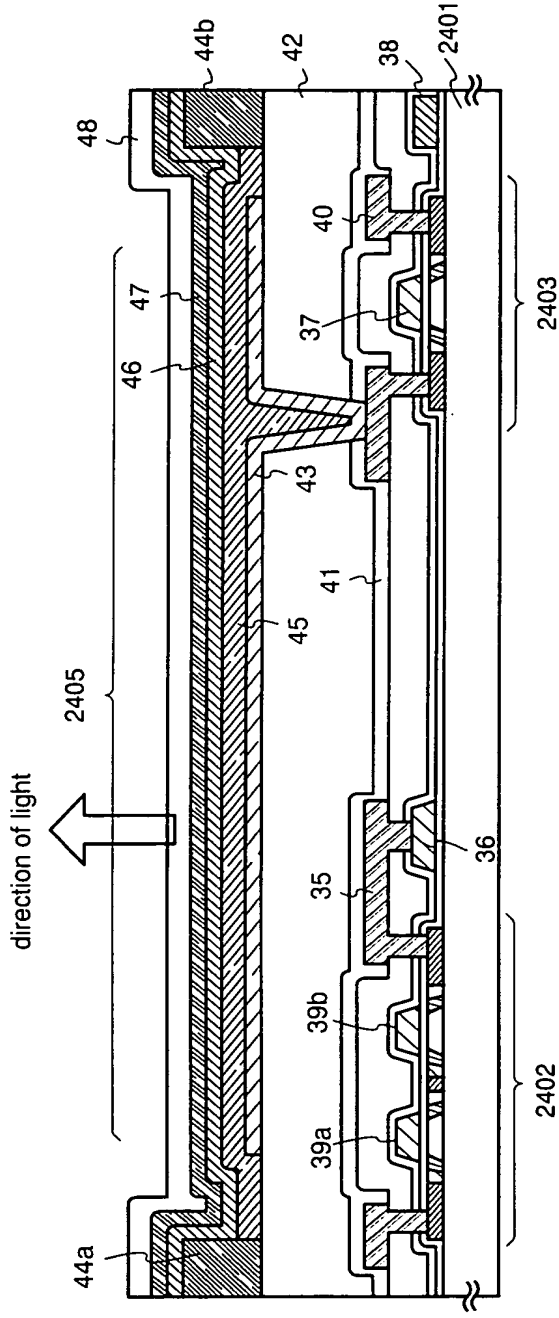


Fig. 19A

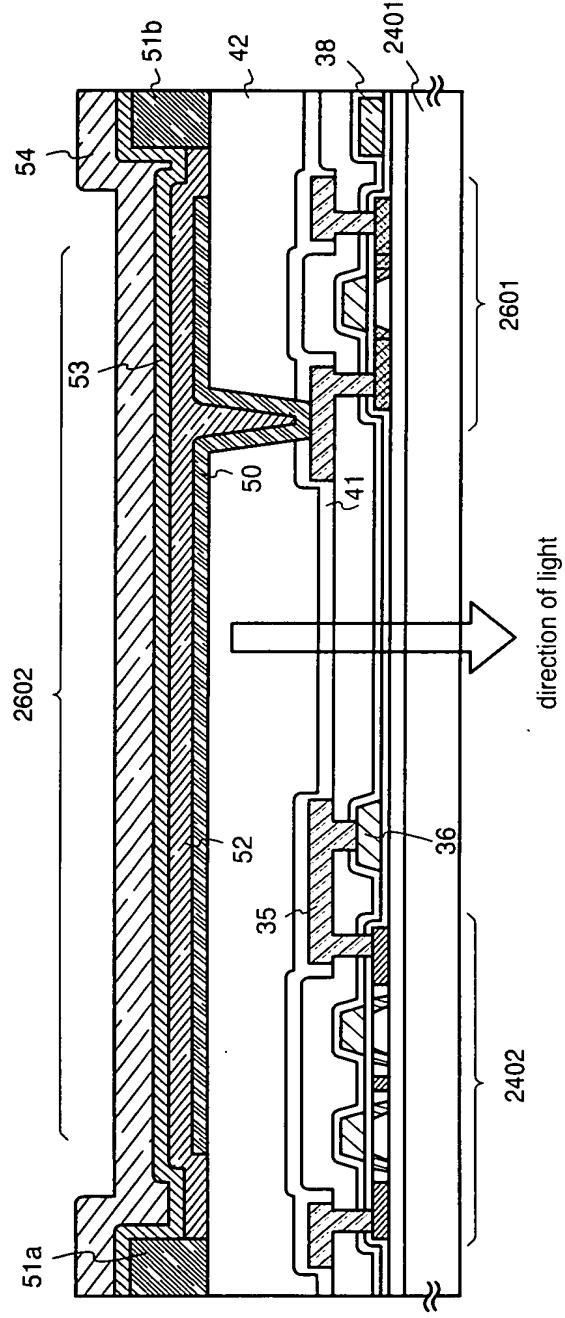


Fig. 19B

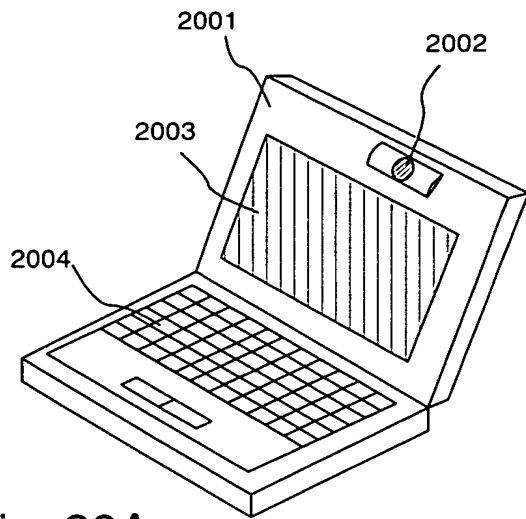


Fig. 20A

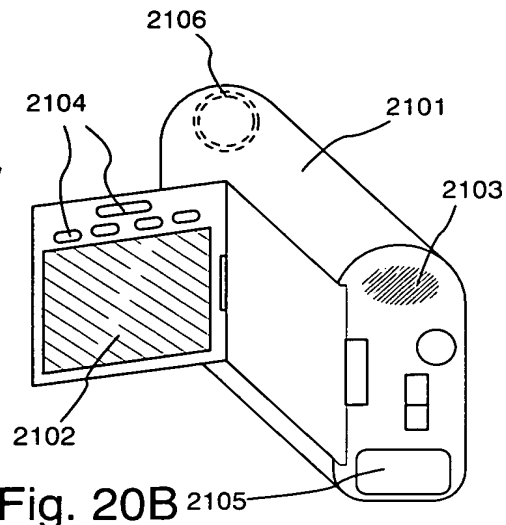


Fig. 20B

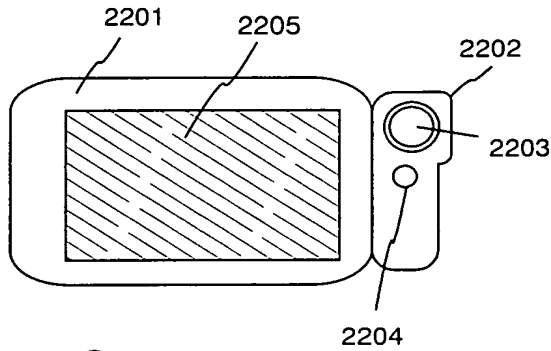


Fig. 20C

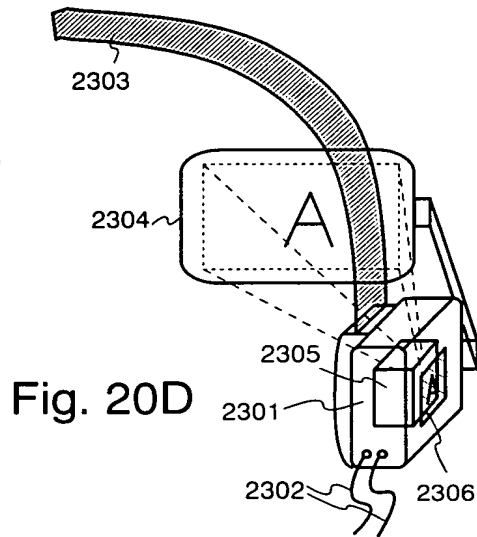


Fig. 20D

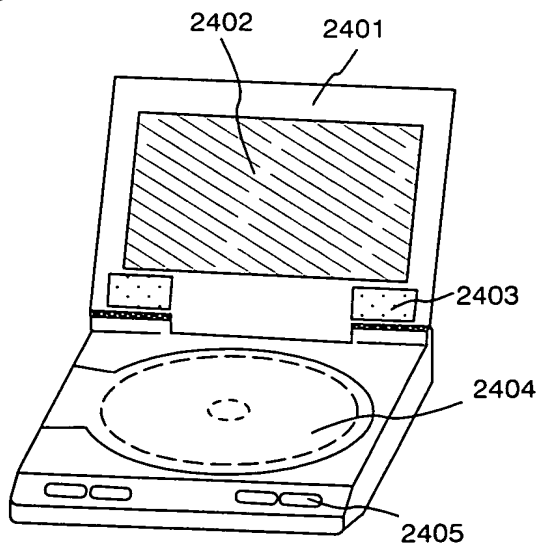


Fig. 20E

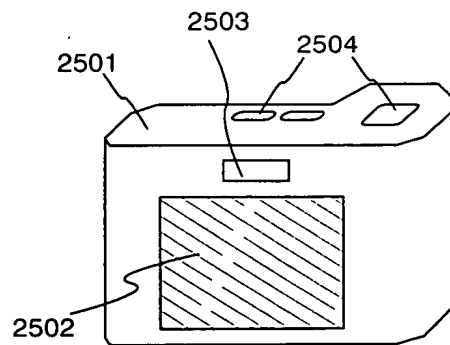


Fig. 20F

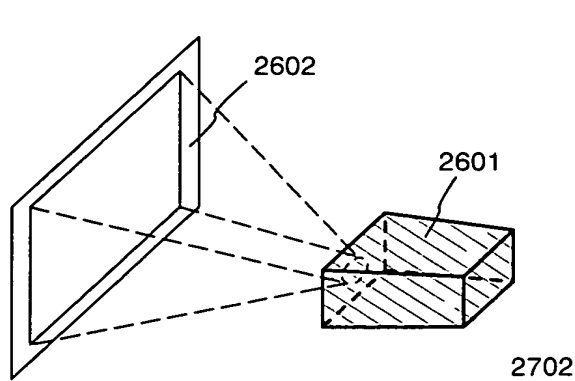


Fig. 21A

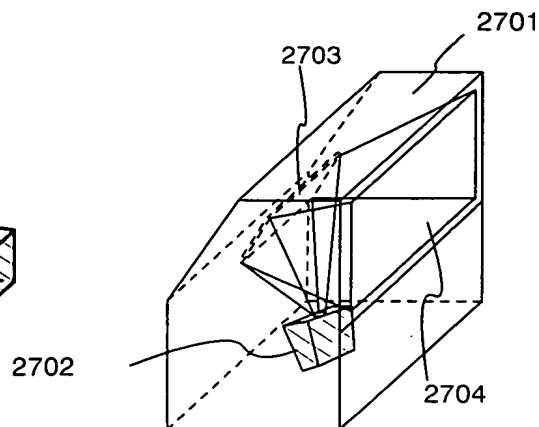


Fig. 21B

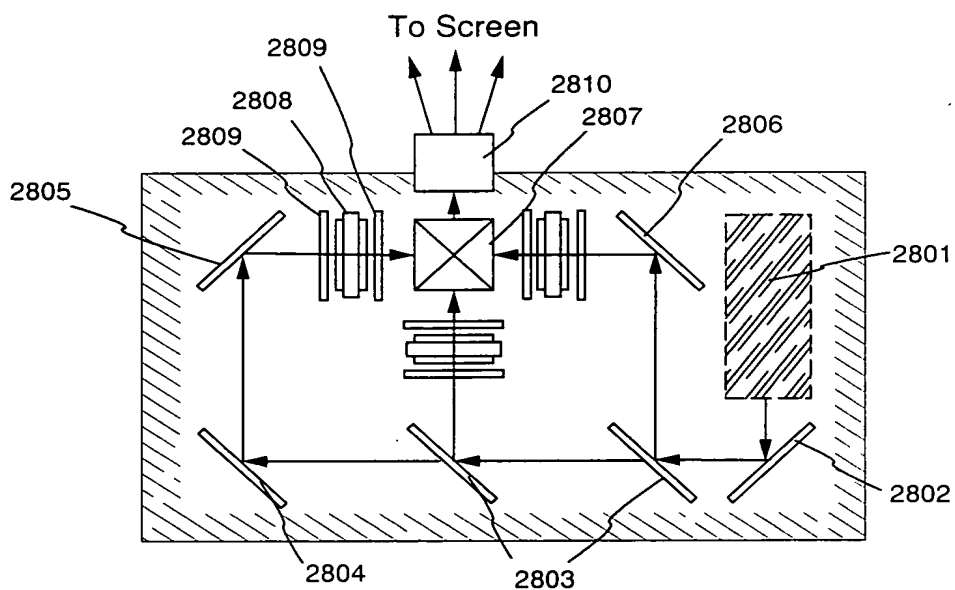


Fig. 21C

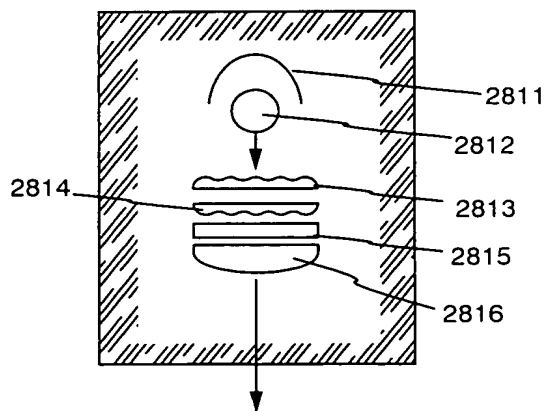


Fig. 21D

Fig. 22A

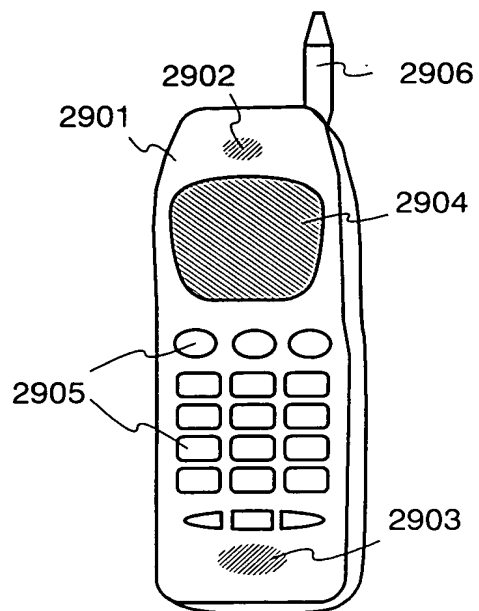


Fig. 22B

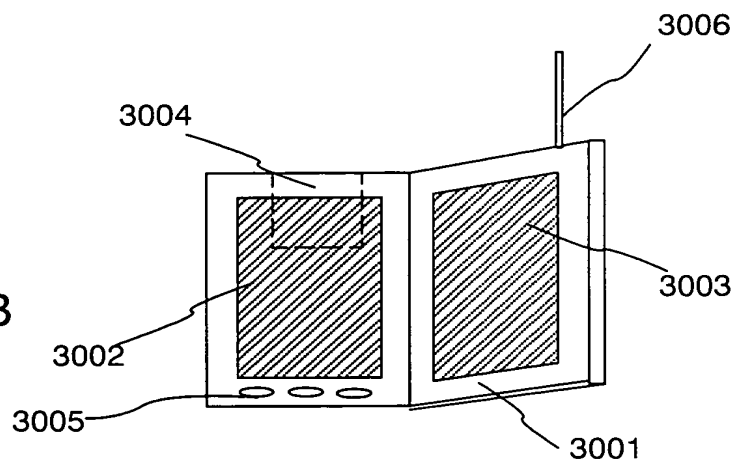
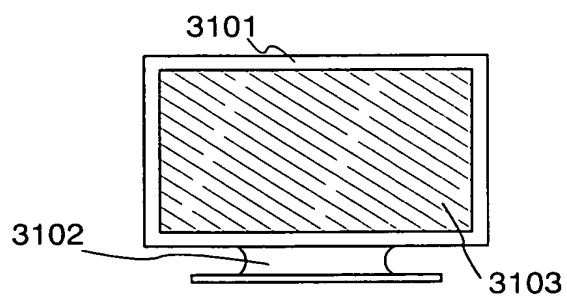


Fig. 22C



FOOT-145460

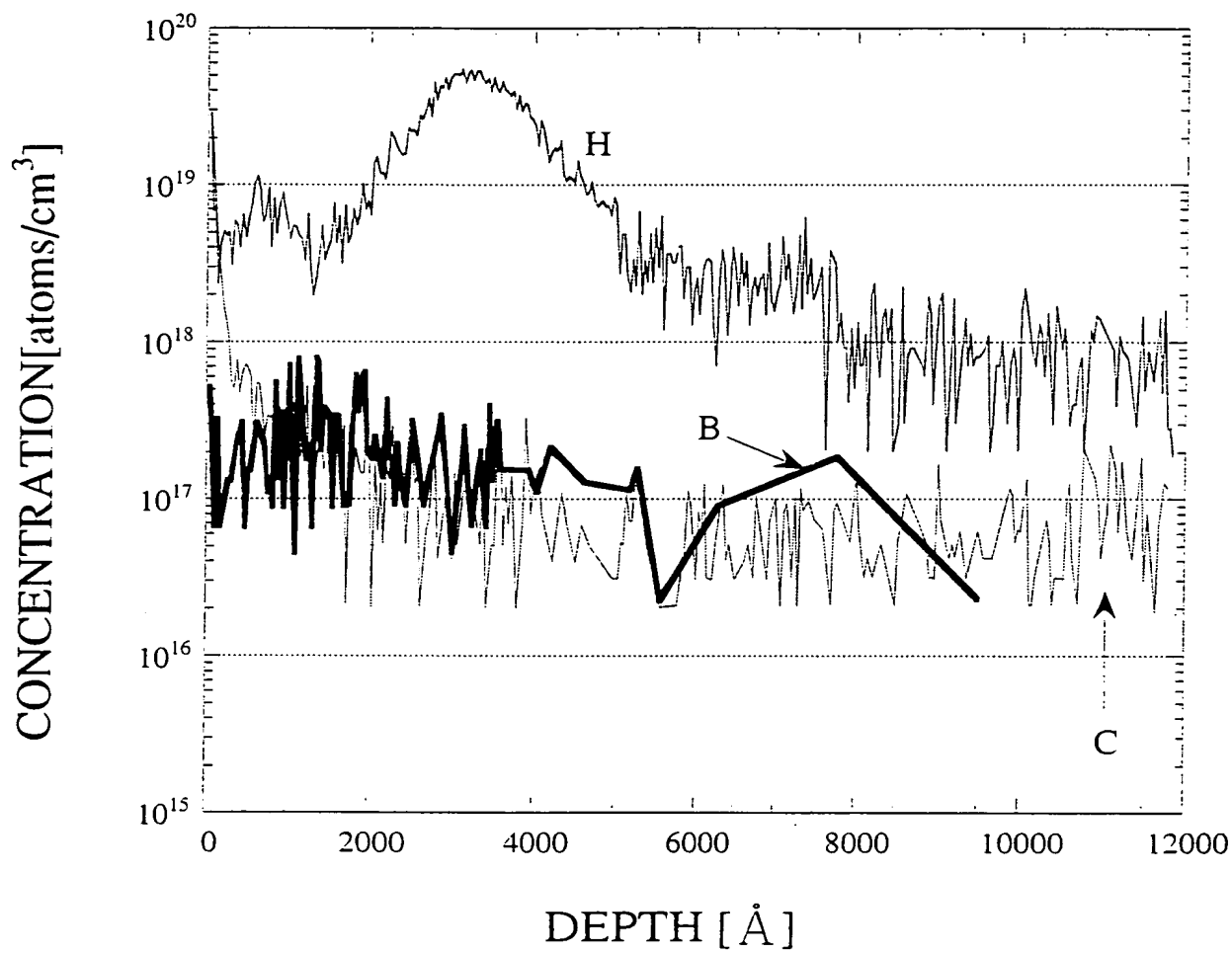


Fig. 23

FOOT-1975/60

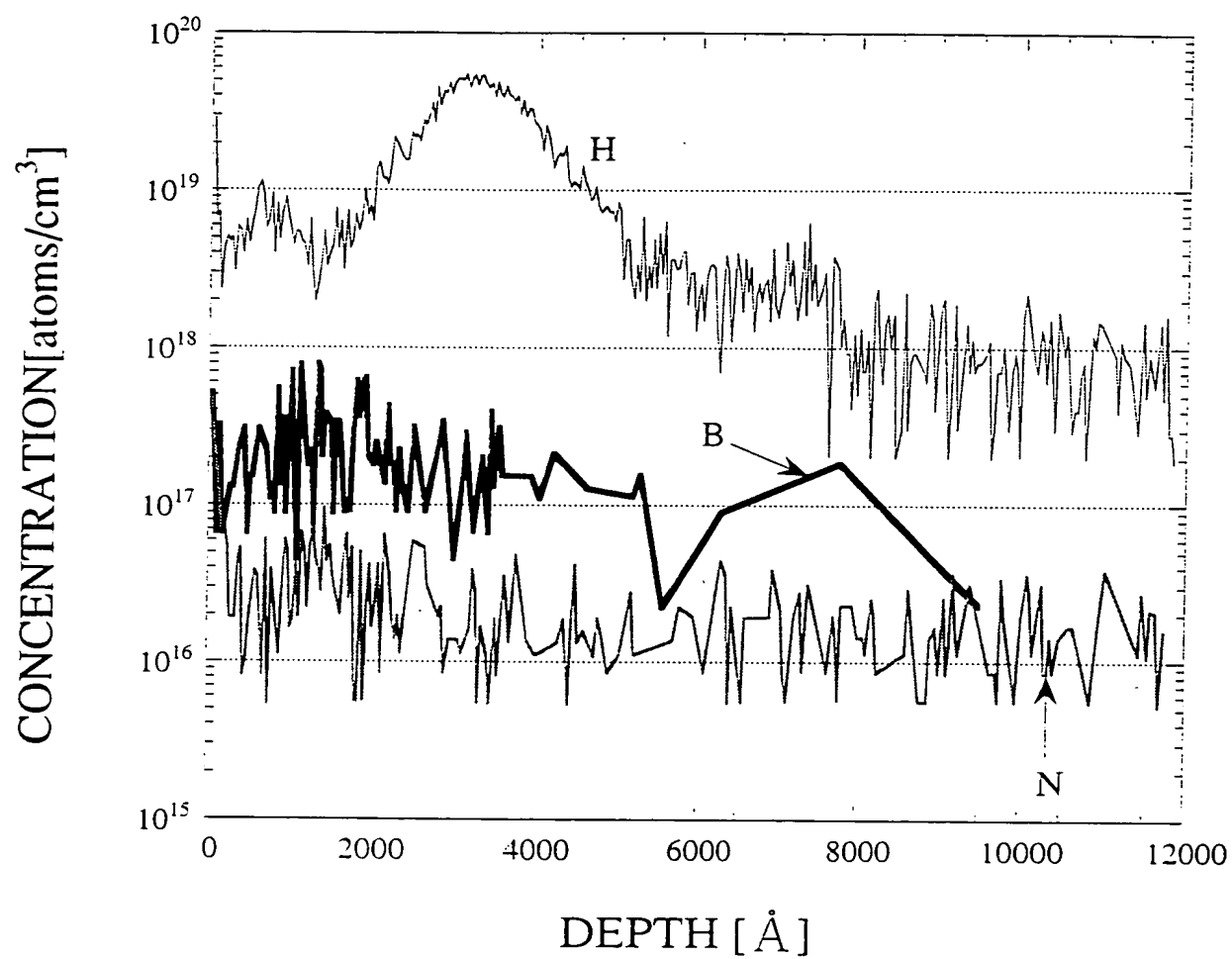


Fig. 24

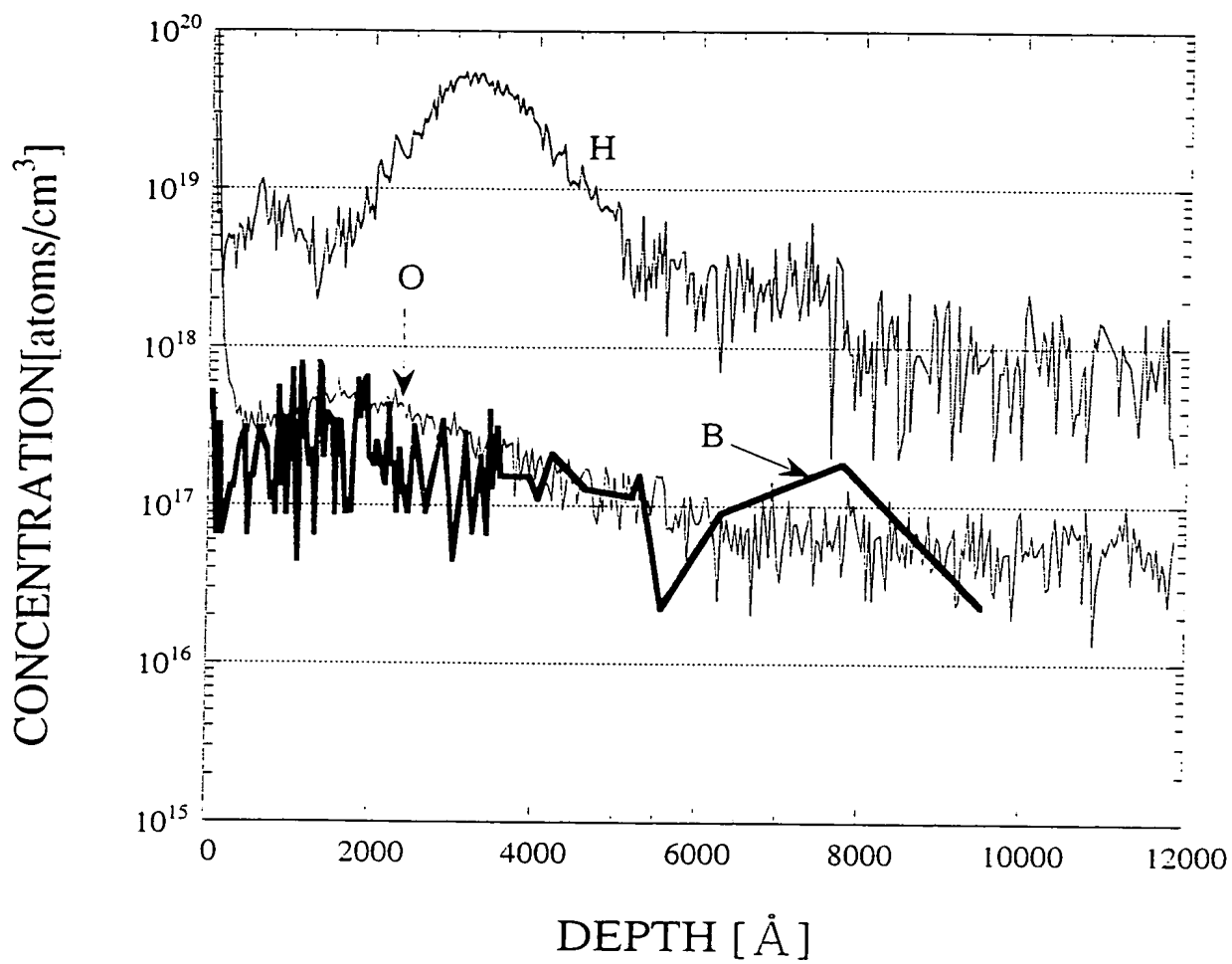


Fig. 25

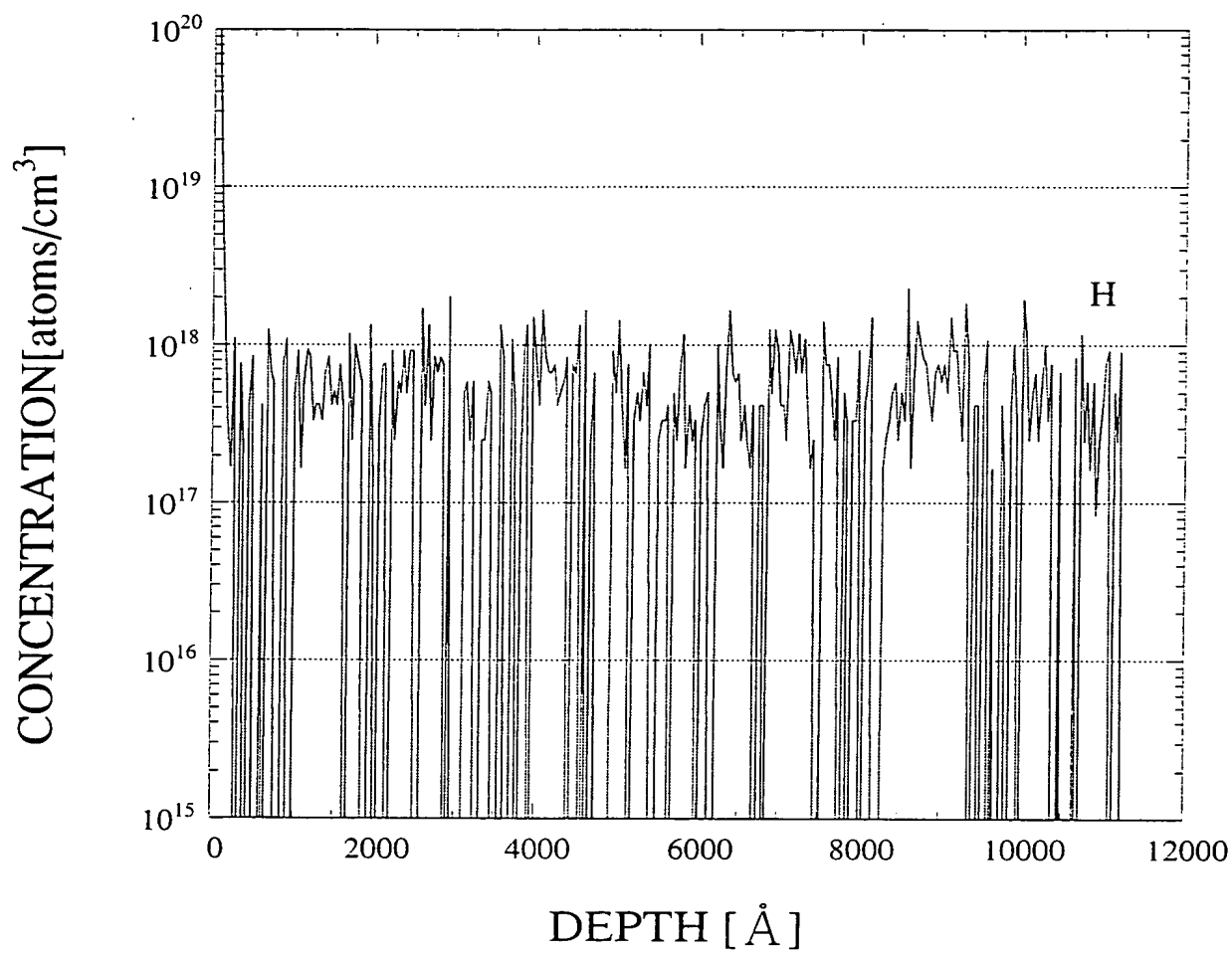


Fig. 26

TUBETO THST9260

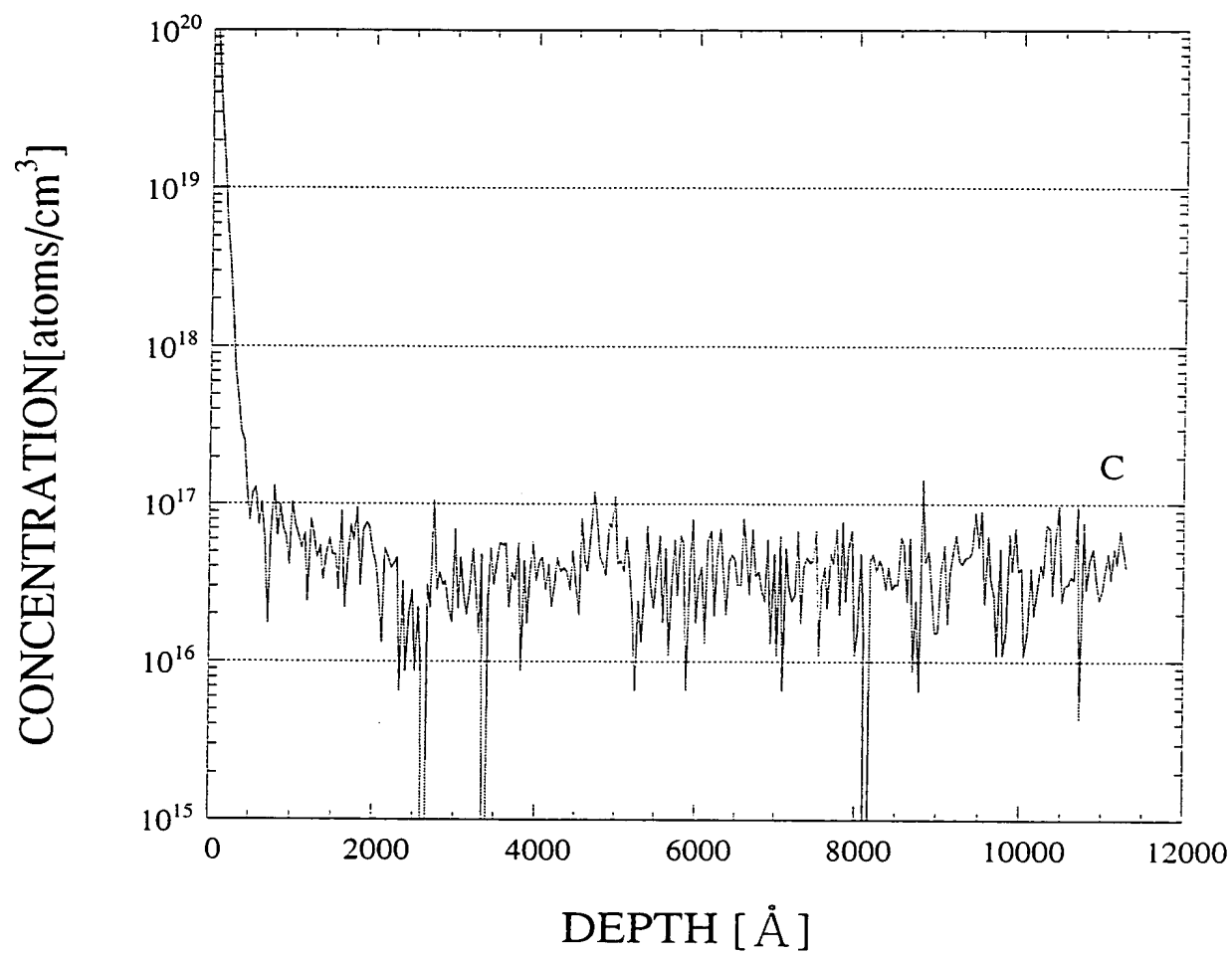


Fig. 27

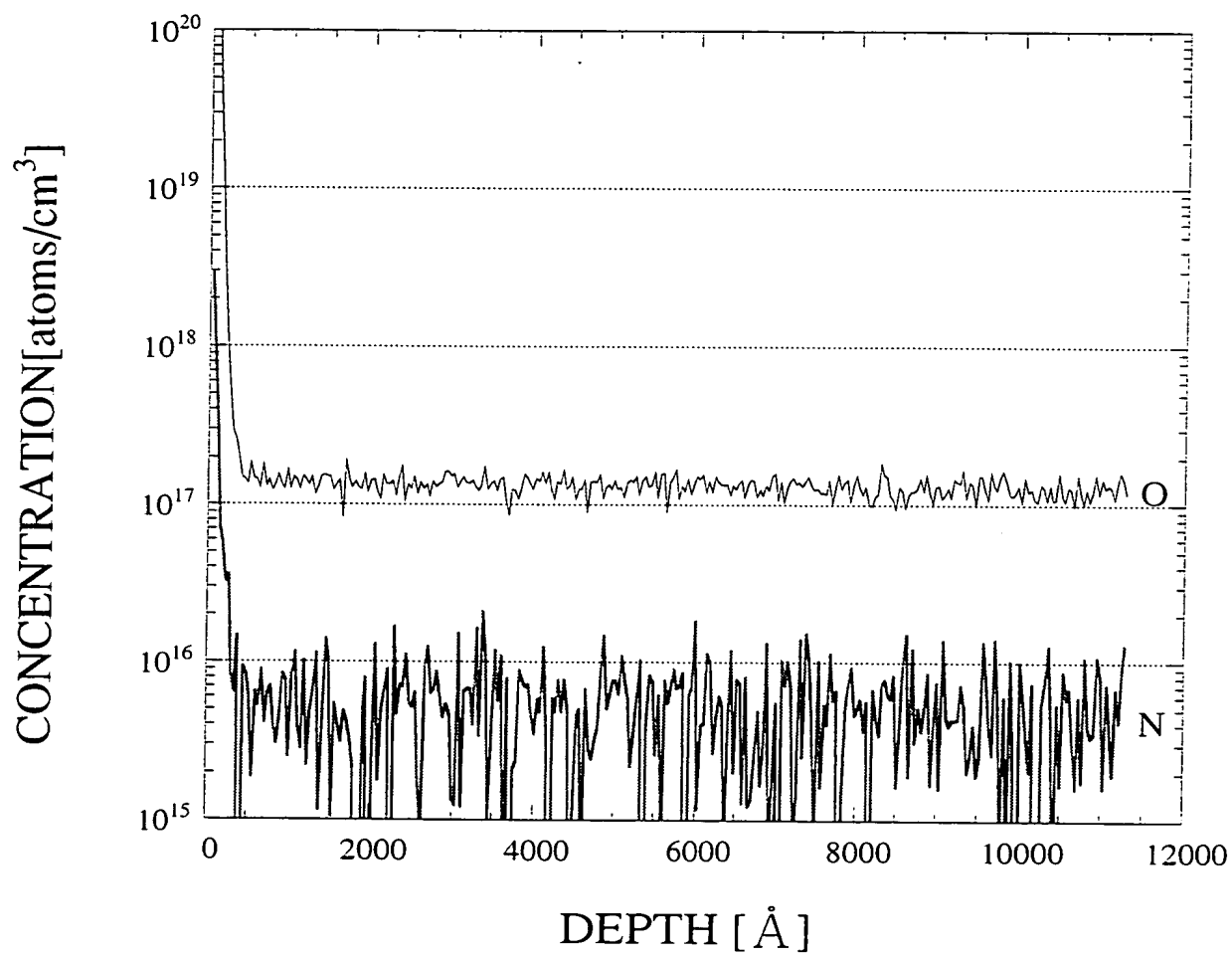
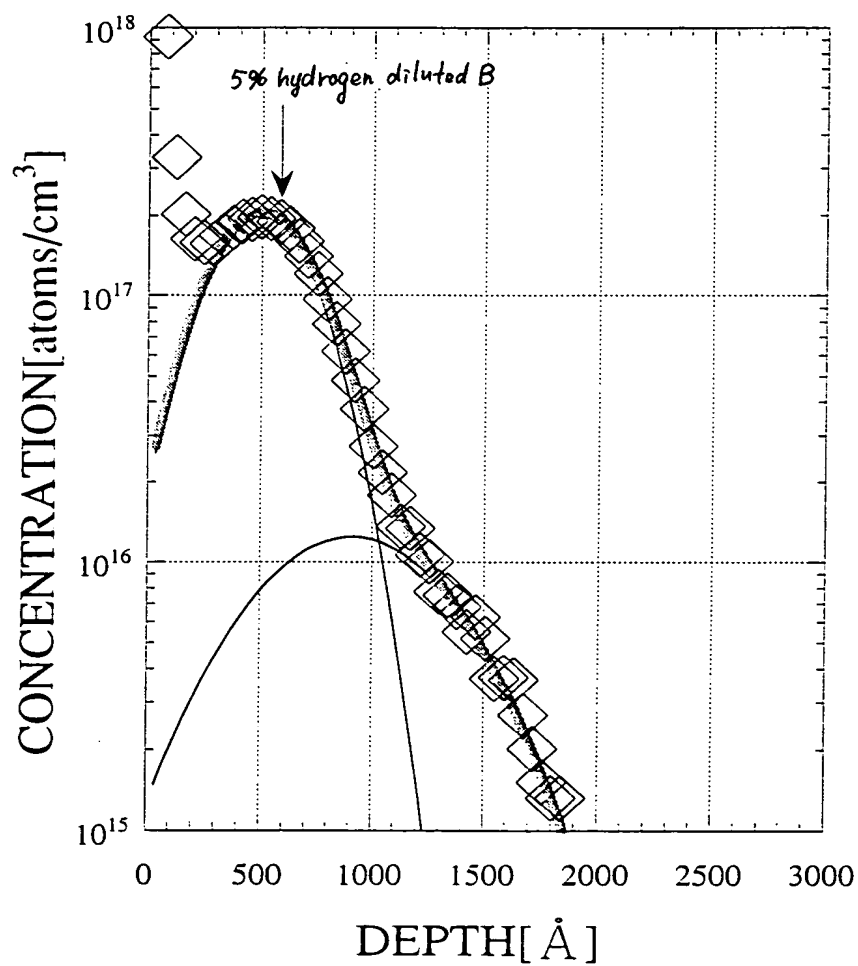


Fig. 28



5% B fitting	
	value
dosage 1	1.1224e+12
dosage 2	1.3183e+11
standard deviation 1	227.08
standard deviation 2	422.75
projected range 1	494.37
projected range 2	908.19
χ^2	0.52998
R	1

Gaussian function fitting

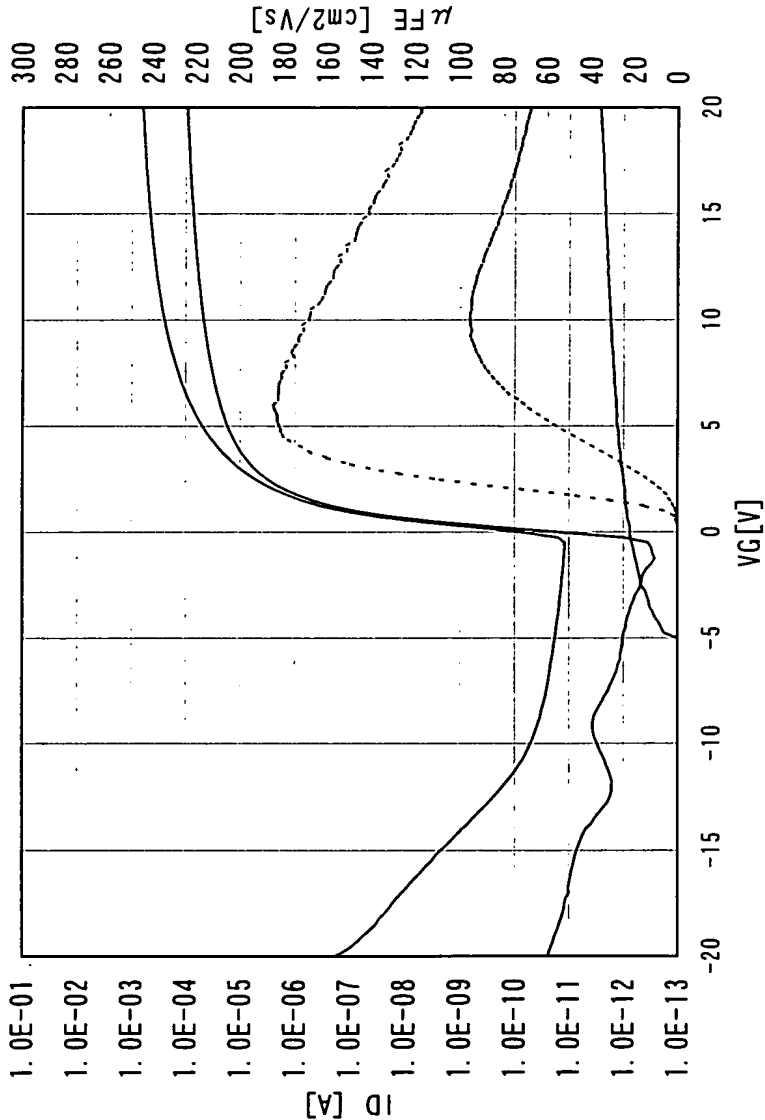
projected range of B at 30kV (Å)
LSS calculation (into Si or SiO₂)

B⁺ : ~ 1000 Å

B₂⁺ : ~ 500 Å

Fig. 29

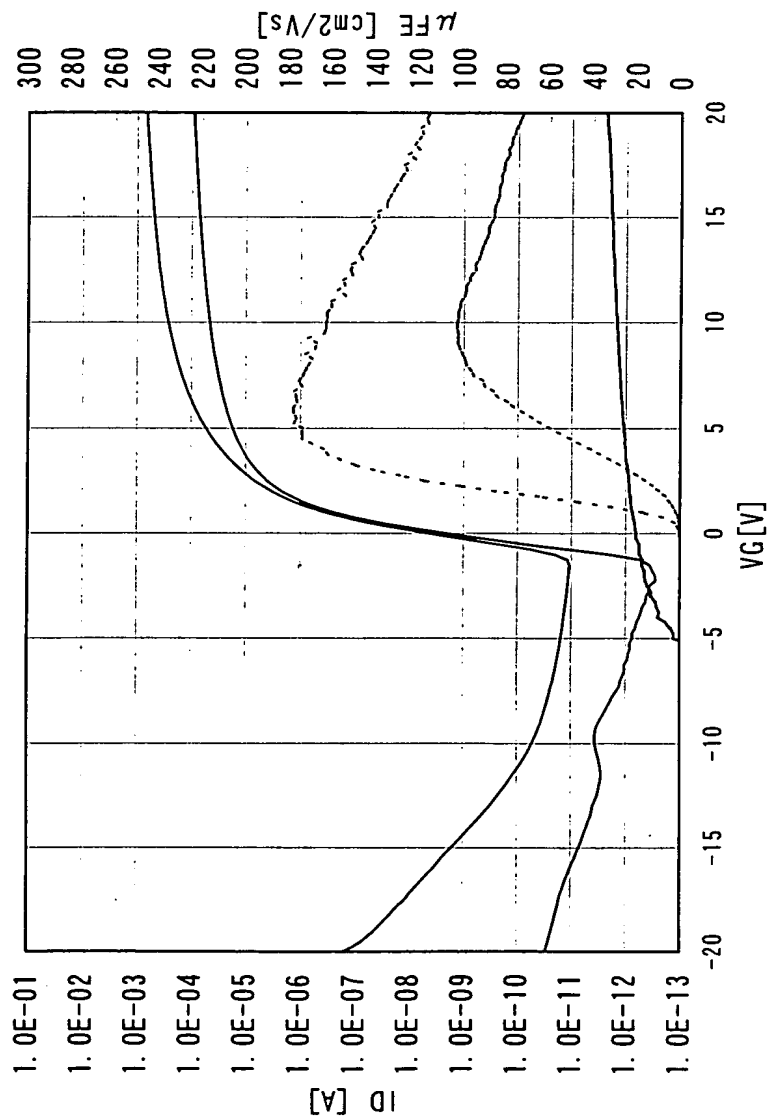
(N-ch, L/W= 7.1/ 7.5, Tox= 115)



parameter		N
channel type		A
kind of TFT		7.1
value of L [um]		7.5
value of W [um]		4.1
dielectric constant		115
thickness of oxide film [um]		
results		
Ion_2	[A]	2.44E-04
Ioff_2	[A]	1.70E-11
Shift_1[V]		-0.231
Vth	[V]	1.430
S-value	[V/dec]	0.201
$\mu_{FE}(\text{max})$	[cm2/Vs]	185.2

Fig. 30

(N-ch, L/W= 7.1/ 7.5, Tox= 115)



parameters		
channel type		N
kind of TFT		A
value of L [μm]		7.1
value of W [μm]		7.5
dielectric constant		4.1
thickness of oxide film [nm]		115
results		
Ion_2		2.65E-04
Ioff_2		1.43E-11
Shift_1[V]		-1.086
Vth		1.361
S-value		0.308
$\mu\text{FE}(\text{max})$		178.5

Fig. 31